

isc Silicon NPN Power Transistor

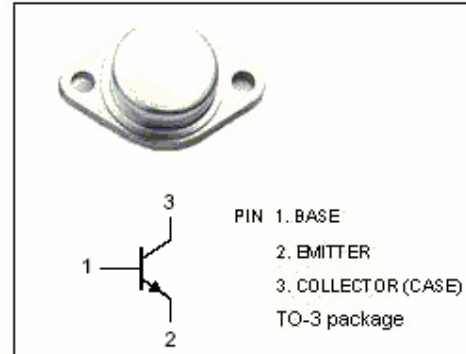
2SD1154

DESCRIPTION

- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 200V$  (Min)
- Wide Area of Safe Operation

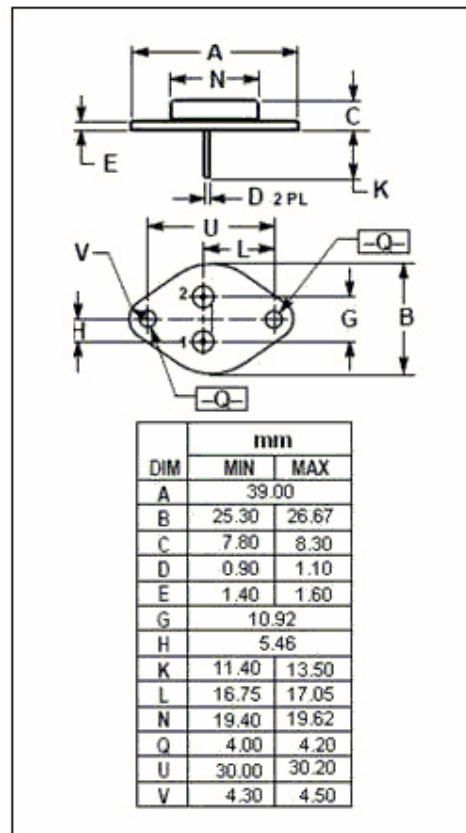
APPLICATIONS

- Designed for horizontal deflection output for B/W TV set.



ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	MAX	UNIT
$V_{CBO}$	Collector-Base Voltage	350	V
$V_{CEO}$	Collector-Emitter Voltage	200	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_c$	Collector Current-Continuous	7	A
$I_{CM}$	Collector Current-Peak	10	A
$P_C$	Collector Power Dissipation @ $T_c=25^{\circ}C$	50	W
$T_j$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-65~150	$^{\circ}C$



**isc Silicon NPN Power Transistor****2SD1154****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	200		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=5\text{mA}; I_C=0$	6		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.4\text{A}$		1	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.4\text{A}$		1.2	V
$I_{CES}$	Collector Cutoff Current	$V_{CE}=350\text{V}; V_{BE}=0$		0.1	mA
		$V_{CE}=350\text{V}; V_{BE}=0; T_C=100^{\circ}\text{C}$		1	
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$		5	mA
$h_{FE}$	DC Current Gain	$I_C=5\text{A}; V_{CE}=4\text{V}$	11	36	
$t_f$	Fall Time	$I_C=5\text{A}; I_B=0.5\text{A}; V_{BB}=-5\text{V}; R_B=0.5\Omega$		0.75	$\mu\text{s}$

◆  **$h_{FE}$  Classifications**

R	Q	P
11-15	11-22	18-36